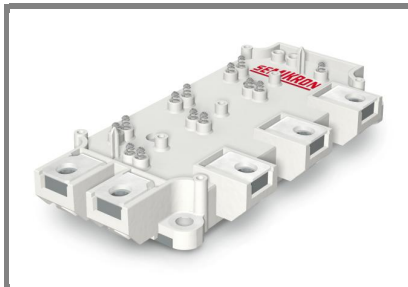


# SEMiX 341D ...



**SEMiX<sup>®</sup> 13s**

## Bridge Rectifier Module (uncontrolled)

### SEMiX 341D

Preliminary Data

### Features

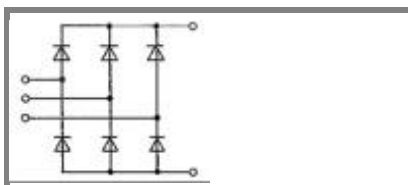
- Terminal height 17 mm
- Chips soldered directly to isolated substrate

### Typical Applications

- Input Bridge Rectifier for
- AC/DC motor control
- power supply

$V_{RSM}$ V	$V_{RRM}, V_{DRM}$ V	$I_D = 340$ A (full conduction) ( $T_c = 85$ °C)
1700	1600	SEMiX 341D16s

Symbol	Conditions	Values	Units
$I_D$	$T_c = 85$ °C	340	A
	$T_c = 100$ °C	290	
$I_{FSM}$	$T_{vj} = 25$ °C; 10 ms	2500	A
	$T_{vj} = 130$ °C; 10 ms	2000	A
$i^2t$	$T_{vj} = 25$ °C; 8,3 ... 10 ms	31200	A <sup>2</sup> s
	$T_{vj} = 130$ °C; 8,3 ... 10 ms	20000	A <sup>2</sup> s
$V_F$	$T_{vj} = 25$ °C; $I_F = 400$ A	max. 1,75	V
$V_{(TO)}$	$T_{vj} = 130$ °C	max. 0,9	V
$r_T$	$T_{vj} = 130$ °C	max. 2,7	mΩ
$I_{RD}$	$T_{vj} = 130$ °C; $V_{DD} = V_{DRM}$ ; $V_{RD} = V_{RRM}$	max. 4,5	mA
$R_{th(j-c)}$	per diode	0,22	K/W K/W
$R_{th(c-s)}$	per module	0,04	K/W
$T_{vj}$		- 40 ... + 130	°C
$T_{stg}$		- 40 ... + 125	°C
$V_{isol}$	a. c. 50 Hz; r.m.s.; 1 s / 1 min.	4800 ( 4000 )	V
$M_s$	(min./max.)	3/5	Nm
$M_t$	(min./max.)	2,5/5	Nm
a		5 * 9,81	m/s <sup>2</sup>
m		300	g
Case	SEMiX 13s		



D

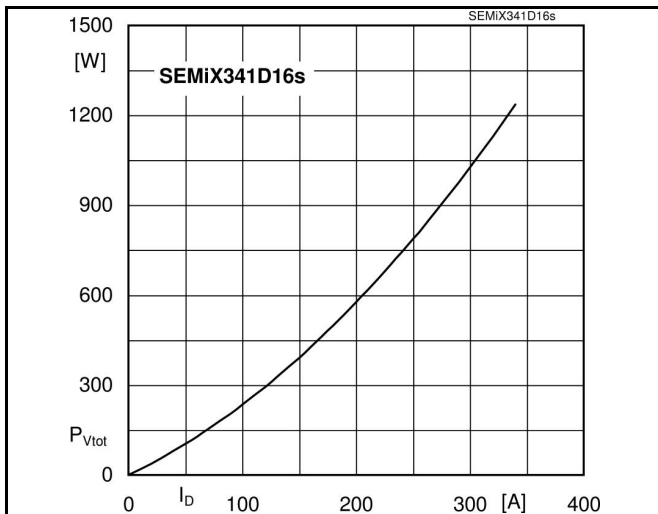


Fig. 4L Power dissipation per module vs. direct current

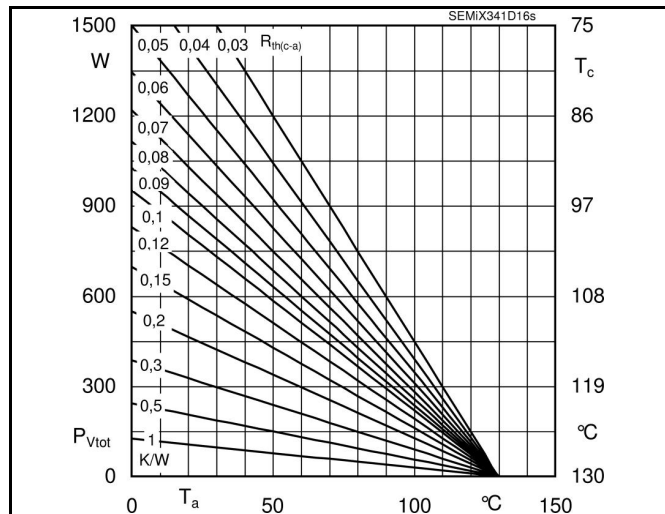


Fig. 4R Power dissipation per module vs. case temperature

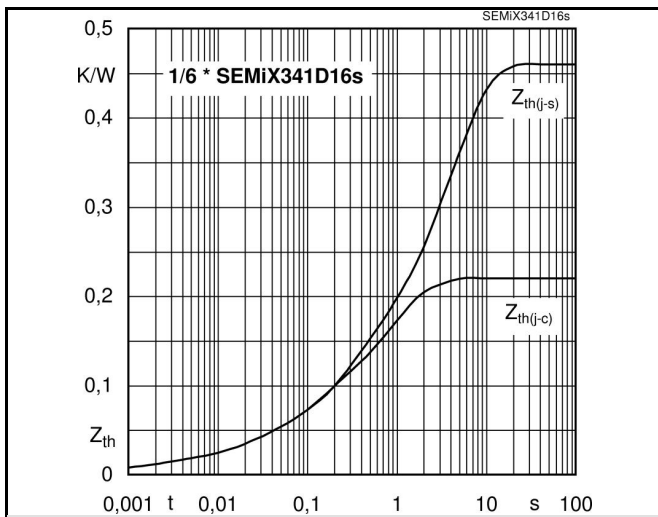


Fig. 6 Transient thermal impedance vs. time

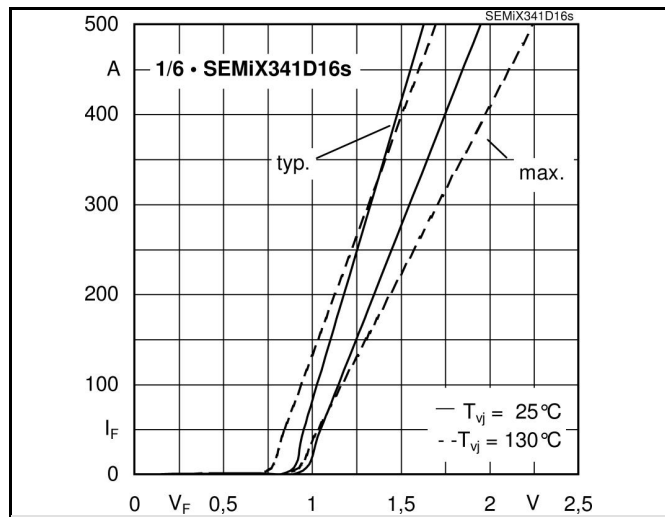


Fig. 7 Forward characteristics

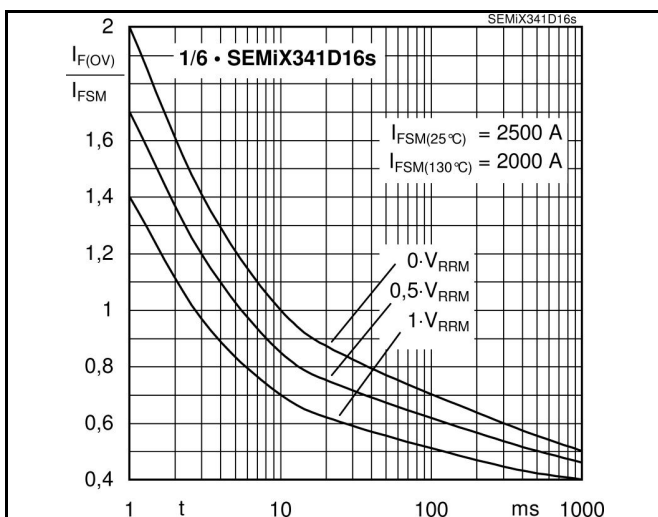
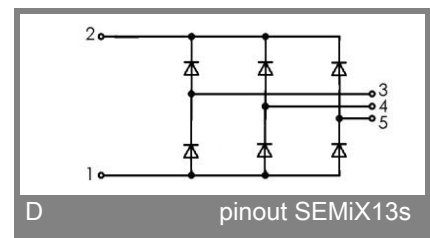
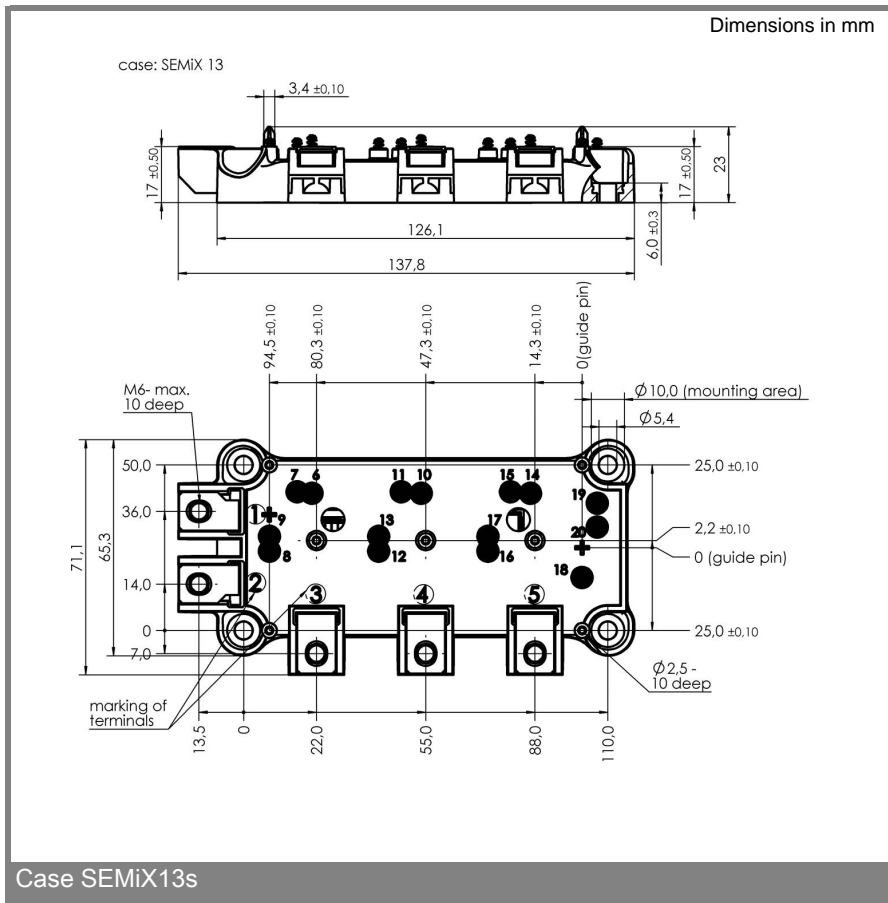


Fig. 8 Surge overload current vs. time

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